

100 Watts - 50 Volts, 3 ms, 30% 960 - 1215 MHz

GENERAL DESCRIPTION

The 0912GN-100LV is an internally matched, COMMON SOURCE, class AB, GaN on SiC HEMT transistor capable of providing over 17 dB gain, 100 Watts of pulsed RF output power at 3ms pulse width, 30% duty factor across the 960 to 1215 MHz band.

55-KR Common Source

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation

Device Dissipation @ 25°C 200W

Maximum Voltage and Current

Drain-Source Voltage (V_{DSS}) 150 V Gate-Source Voltage (V_{GS}) -8 to +0 V

Maximum Temperatures

Storage Temperature (T_{STG}) -55 to +125° C Operating Junction Temperature +250 °C



ELECTRICAL CHARACTERISTICS @ 25°C

Symbol	Characteristics	Test Conditions	Min	Тур	Max	Units
Pout	Output Power	Pin=2W Freq=960,1090,1215 MHz	100	110		W
Gp	Power Gain	Pin=2W Freq=960,1090,1215 MHz	17	17.5		dB
ηd	Drain Efficiency	Pin=2W Freq=960,1090,1215 MHz	55	59		%
Dr	Droop	Pin=2W Freq=960,1090,1215 MHz			0.8	dB
VSWR-T	Load Mismatch Tolerance	Pout=100W, Freq= 1090MHz			3:1	
Өјс	Thermal Resistance	Pulse Width=3mS, Duty=30%			1.44	°C/W

Bias Condition: Vdd=+50V, Idq=70mA constant current (Vgs= -2.0 ~ -4.5V typical)

FUNCTIONAL CHARACTERISTICS @ 25°C

$I_{D(Off)}$	Drain leakage current	$V_{gS} = -8V, V_D = 50V$		15	mA
$I_{G(Off)}$	Gate leakage current	$V_{gS} = -8V, V_D = 0V$		12	mA
BV _{DSS}	Drain-source breakdown voltage	$V_{gs} = -8V, I_D = 30mA$	150		V

Export Classification: ER99



100 Watts - 50 Volts, 3 ms, 30% 960 - 1215 MHz

TYPICAL BROAD BAND PERFORMACE DATA

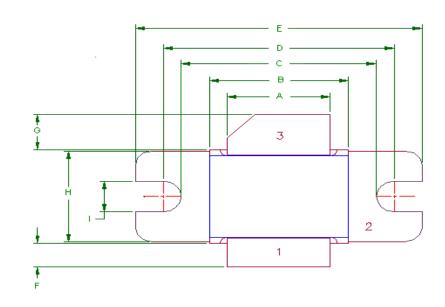
Frequency	Pin (W)	Pout (W)	ld (A)	RL (dB)	Nd (%)	G (dB)	Droop (dB)
960 MHz	2	130	1.23	-7	62	18.2	.6
1090 MHz	2	125	1.14	-7	68	18	.4
1215 MHz	2	110	1.12	-10	59	17.5	.6

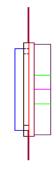
Test Circuit Available Upon Request



100 Watts - 50 Volts, 3 ms, 30% 960 - 1215 MHz

55-KR PACKAGE DIMENSION







1 = Gate 2 = Source 3 = Drain

Dimension	Min (mil)	Min (mm)	Max (mil)	Max (mm)
Α	370	9.40	372	9.44
В	498	12.65	500	12.7
С	700	17.78	702	17.83
D	830	21.08	832	21.13
E	1030	26.16	1032	26.21
F	101	2.56	102	2.59
G	151	3.84	152	3.86
Н	385	9.78	387	9.83
I	130	3.30	132	3.35
J	003	.076	004	0.10
K	135	3.43	137	3.48
L	105	2.67	107	2.72
M	085	2.16	86	2.18
N	065	1.65	66	1.68



100 Watts - 50 Volts, 3 ms, 30% 960 - 1215 MHz

The information contained in the document is PROPRIETARY AND CONFIDENTIAL information of Microsemi and cannot be copied, published, uploaded, posted, transmitted, distributed or disclosed or used without the express duly signed written consent of Microsemi If the recipient of this document has entered into a disclosure agreement with Microsemi, then the terms of such Agreement will also apply. This document and the information contained herein may not be modified, by any person other than authorized personnel of Microsemi. No license under any patent, copyright, trade secret or other intellectual property right is granted to or conferred upon you by disclosure or delivery of the information, either expressly, by implication, inducement, estoppels or otherwise. Any license under such intellectual property rights must be approved by Microsemi in writing signed by an officer of Microsemi

Microsemi reserves the right to change the configuration, functionality and performance of its products at anytime without any notice. This product has been subject to limited testing and should not be used in conjunction with life-support or other mission-critical equipment or applications. Microsemi assumes no liability whatsoever, and Microsemi disclaims any express or implied warranty, relating to sale and/or use of Microsemi products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright or other intellectual property right. The product is subject to other terms and conditions which can be located on the Web at http://www.microsemi.com/legal/tnc.asp.

Revision History

Revision Level / Date	Para. Affected	Description
0.1 / 10 July 2014	-	Initial Preliminary Release